Laurent Cario

List of Publications by Year
in descending order

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154 papers	4,927 citations	76196 40 h-index	110170 64 g-index
161 all docs	161 docs citations	161 times ranked	5967 citing authors

#	Article	IF	Citations
1	Self-Assembly and Characterization of Layered Double Hydroxide/DNA Hybrids. Nano Letters, 2006, 6, 199-204.	4.5	266
2	A Leakyâ€Integrateâ€andâ€Fire Neuron Analog Realized with a Mott Insulator. Advanced Functional Materials, 2017, 27, 1604740.	7.8	186
3	Superconducting Density of States and Vortex Cores of 2H-<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>NbS</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review Letters, 2008, 101, 166407.	2.9	183
4	Coherent long-range magnetic bound states in aÂsuperconductor. Nature Physics, 2015, 11, 1013-1016.	6.5	155
5	Resistive Switching in Mott Insulators and Correlated Systems. Advanced Functional Materials, 2015, 25, 6287-6305.	7.8	130
6	Electricâ€Fieldâ€Induced Resistive Switching in a Family of Mott Insulators: Towards a New Class of RRAM Memories. Advanced Materials, 2010, 22, 5193-5197.	11.1	125
7	Amplitude Higgs mode in the<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi><mml:msub><mml:mi>Ta</mml:mi><mml:mn>4</mml:mn></mml:msub><mml:msub><mml:mi>Se</mml:mi><mml:mn>8</mml:mn></mml:msub></mml:math>. Physical Review B, 2014, 89, .	3.7	124
8	Ruthenium polypyridine complexes as sensitizers in NiO based p-type dye-sensitized solar cells: Effects of the anchoring groups. Journal of Photochemistry and Photobiology A: Chemistry, 2011, 219, 235-242.	2.0	117
9	P-Type Nitrogen-Doped ZnO Nanoparticles Stable under Ambient Conditions. Journal of the American Chemical Society, 2012, 134, 464-470.	6.6	115
10	CuGaO2: a promising alternative for NiO in p-type dye solar cells. Journal of Materials Chemistry, 2012, 22, 14353.	6.7	114
11	Universal Electricâ€Fieldâ€Driven Resistive Transition in Narrowâ€Gap Mott Insulators. Advanced Materials, 2013, 25, 3222-3226.	11.1	114
12	Structure and Magnetic Properties of Oxychalcogenides A₂F₂Fe₂OQ₂ (A = Sr, Ba; Q = S, Se) with Fe₂O Square Planar Layers Representing an Antiferromagnetic Checkerboard Spin Lattice. Journal of the American Chemical Society, 2008, 130, 8261-8270.	6.6	105
13	Avalanche breakdown in GaTa4Se8â^’xTex narrow-gap Mott insulators. Nature Communications, 2013, 4, 1722.	5.8	100
14	Strong enhancement of superconductivity at high pressures within the charge-density-wave states of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mtext>â^’</mml:mtext></mml:mrow></mml:math><mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mtext>â^’</mml:mtext></mml:mrow></mml:math>. Physical Review B, 2016, 93, .	3.7	96
15	Strong anharmonicity induces quantum melting of charge density wave in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>â^’</mml:mo></mml:mrow></mml:math> pressure. Physical Review B, 2015, 92, .	3.7	93
16	Tuning the size and color of the p-type wide band gap delafossite semiconductor CuGaO2 with ethylene glycol assisted hydrothermal synthesis. Journal of Materials Chemistry, 2008, 18, 5647.	6.7	87
17	Simple and Reproducible Procedure to Prepare Self-Nanostructured NiO Films for the Fabrication of P-Type Dye-Sensitized Solar Cells. Inorganic Chemistry, 2009, 48, 8245-8250.	1.9	85
18	Origin of the Black Color of NiO Used as Photocathode in p-Type Dye-Sensitized Solar Cells. Journal of Physical Chemistry C, 2013, 117, 22478-22483.	1.5	76

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19	Electricâ€Pulseâ€driven Electronic Phase Separation, Insulatorâ€“Metal Transition, and Possible Superconductivity in a Mott Insulator. Advanced Materials, 2008, 20, 2760-2765.	11.1	70
20	Anharmonic suppression of charge density waves in 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>H</mml:mi></mml:mrow></mml:math>-NbS<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow [illegible] Physical Review B, 2012, 86, .	1.1	66
21	Pressure dependence of superconducting ground state and upper critical field of 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>H</mml:mi></mml:math>-NbS<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow [illegible] Physical Review B, 2013, 87, .	1.1	63
22	Resistive Switching at the Nanoscale in the Mott Insulator Compound GaTa₄Se₈. Nano Letters, 2013, 13, 3648-3653.	4.5	62
23	Ultrafast Formation of a Charge Density Wave State in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mn>1</mml:mn><mml:mi>T</mml:mi><mml:mtext>â”</mml:mtext><mml:msub><mml [illegible] : Observation at Nanometer Scales Using Time-Resolved X-Ray Diffraction. Physical Review Letters, 2017, 118, 247401.	2.9	60
24	Quasiparticle spectra of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mo>â’</mml:m Two-band superconductivity and the role of tunneling selectivity. Physical Review B, 2015, 92, .	1.1	56
25	Rational design of new inorganic compounds with the ZrSiCuAs structure type using 2D building blocks. Journal of Materials Chemistry, 2005, 15, 3525.	6.7	55
26	Facile Synthesis of BiCuOS by Hydrothermal Methods. Inorganic Chemistry, 2007, 46, 10741-10748.	1.9	55
27	Half-Metallic Ferromagnetism and Large Negative Magnetoresistance in the New Lacunar Spinel GaTi₃VS₈. Journal of the American Chemical Society, 2010, 132, 5704-5710.	6.6	55
28	Specific heat measurements of a superconducting<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>NbS</mml:mtext></mml:mrow><mml:mn>2</mml:mn></mml:ms crystal in an external magnetic field: Energy gap structure. Physical Review B, 2010, 82, .	1.1	52
29	First-Order Insulator-to-Metal Mott Transition in the Paramagnetic 3D System<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>GaTa</mml:mi></mml:mrow><mml:mrow><mml:mn>4</mml:mn> Physical Review Letters, 2014, 113, 086404.	2.9	52
30	Orbital-Ordering-Driven Multiferroicity and Magnetoelectric Coupling in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mi>GeV</mml:mi></mml:mrow><mml:mrow><mml:mn>4</mml:mn> mathvariant="normal">S</mml:mi></mml:mrow><mml:mrow><mml:mn>8</mml:mn></mml:mrow></mml:msub></mml:mrow></mml: Physical Review Letters, 2014, 113, 137602.	2.9	51
31	Crystal structures of two new oxysulfides La5Ti2MS5O7 (M=Cu, Ag): evidence of anionic segregation. Journal of Solid State Chemistry, 2004, 177, 2810-2817.	1.4	49
32	Optical Conductivity Measurements of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>GaTa</mml:mi><mml:mn>4</mml:mn></mml:msub><mml:msub><mml:mi>Se</mml:mi><mml: High Pressure: Evidence of a Bandwidth-Controlled Insulator-to-Metal Mott Transition. Physical Review Letters, 2013, 110, 037401.	2.9	49
33	Impact of Mg Doping on Performances of CuGaO₂ Based p-Type Dye-Sensitized Solar Cells. Journal of Physical Chemistry C, 2014, 118, 54-59.	1.5	47
34	CuO nanomaterials for p-type dye-sensitized solar cells. RSC Advances, 2016, 6, 112765-112770.	1.7	46
35	Designing New Inorganic Compounds from 2D Building Blocks. Chemistry of Materials, 2005, 17, 234-236.	3.2	45
36	Chiral charge order in the superconductor 2H-TaS₂. New Journal of Physics, 2011, 13, 103020.	1.2	45

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37	Nonthermal and purely electronic resistive switching in a Mott memory. Physical Review B, 2014, 90, .	1.1	44
38	Higgs-mode radiance and charge-density-wave order in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi></mml:mrow></mml:math>-TaSe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review B, 2018, 97, .	1.1	44
39	Hole conductivity and acceptor density of p-type CuGaO2 nanoparticles determined by impedance spectroscopy: The effect of Mg doping. Electrochimica Acta, 2013, 113, 570-574.	2.6	43
40	Copper borate as a photocathode in p-type dye-sensitized solar cells. RSC Advances, 2016, 6, 1549-1553.	1.7	41
41	Traces of charge density waves in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>NbS</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>. Physical Review B, 2018, 97, .	1.1	41
42	Engineering Processes at the Interface of pâ€Semiconductor for Enhancing the Open Circuit Voltage in pâ€Type Dyeâ€Sensitized Solar Cells. Advanced Energy Materials, 2017, 7, 1601776.	10.2	36
43	Inorganic Molybdenum Clusters as Lightâ€Harvester in All Inorganic Solar Cells: A Proof of Concept. ChemistrySelect, 2016, 1, 2284-2289.	0.7	35
44	Design of a New Family of Inorganic Compounds Ae2F2SnX3(Ae = Sr, Ba; X = S, Se) Using Rock Salt and Fluorite 2D Building Blocks. Inorganic Chemistry, 2006, 45, 917-922.	1.9	33
45	Scanning tunneling measurements of layers of superconducting 2<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mi>H</mml:mi></mml:math>-TaSe<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mn>2</mml:mn></mml:msub></mml:math>: Evidence for a zero-bias anomaly in single layers. Physical Review B, 2013, 87, .	1.1	33
46	How a dc Electric Field Drives Mott Insulators Out of Equilibrium. Physical Review Letters, 2018, 121, 016601.	2.9	33
47	Ae2Sb2X4F2(Ae = Sr, Ba):Â New Members of the Homologous Series Ae2M1+nX3+nF2Designed from Rock Salt and Fluorite 2D Building Blocks. Inorganic Chemistry, 2006, 45, 2713-2717.	1.9	32
48	Stability and charge transfer in the misfit compound (LaS)(SrS)0.2CrS2: Ab initio band-structure calculations. Physical Review B, 1997, 55, 9409-9414.	1.1	31
49	Direct experimental observation of the molecular J effâ€‰=â€‰3/2 ground state in the lacunar spinel GaTa4Se8. Nature Communications, 2017, 8, 782.	5.8	30
50	Synthesis of p-Type Transparent LaOCuS Nanoparticles via Soft Chemistry. Inorganic Chemistry, 2010, 49, 3074-3076.	1.9	29
51	Strain wave pathway to semiconductor-to-metal transition revealed by time-resolved X-ray powder diffraction. Nature Communications, 2021, 12, 1239.	5.8	29
52	Electric-pulse-induced resistive switching and possible superconductivity in the Mott insulator GaTa4Se8. Microelectronic Engineering, 2008, 85, 2430-2433.	1.1	28
53	Control of the Electronic Properties and Resistive Switching in the New Series of Mott Insulators GaTa₄Se_{8â€“y}Te_y (0 â‰¤ y â‰¤ 6.5). Chemistry of Materials, 2011, 23, 2611-2618.	3.2	28
54	Charge Transfer in Misfit Layer Chalcogenides, [(MX)ⁿ]^{1+x}(TX²)^m: a Key for Understanding their Stability and Properties. Molecular Crystals and Liquid Crystals, 2000, 341, 1-8.	0.3	27

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55	Metalâ^'Metal Bonding and Correlated Metallic Behavior in the New Deficient Spinel Ga0.87Ti4S8. Chemistry of Materials, 2008, 20, 2382-2387.	3.2	27
56	Cu2O@CuO core-shell nanoparticles as photocathode for p-type dye sensitized solar cell. Journal of Alloys and Compounds, 2018, 769, 605-610.	2.8	26
57	Mott insulators: A large class of materials for Leaky Integrate and Fire (LIF) artificial neuron. Journal of Applied Physics, 2018, 124, .	1.1	24
58	Evidence of a Mixed-Valence State for Europium in the Misfit Layer Compound [(EuS)1.5]1.15NbS2 by Means of a Superspace Structural Determination, MÃ¶ssbauer Spectroscopy, and Magnetic Measurements. Journal of Solid State Chemistry, 1999, 147, 58-67.	1.4	23
59	Ln3T2N6 (Ln=La, Ce, Pr; T=Ta, Nb), a New Family of Ternary Nitrides Isotypic to a High Tc Cuprate Superconductor. Journal of Solid State Chemistry, 2001, 162, 90-95.	1.4	23
60	Mixed-Valence State of Europium in the Misfit Layer Compound (EuS)1.173NbS2. Chemistry of Materials, 2003, 15, 943-950.	3.2	23
61	Electricâ€Fieldâ€Assisted Nanostructuring of a Mott Insulator. Advanced Functional Materials, 2009, 19, 2800-2804.	7.8	23
62	First evidence of resistive switching in polycrystalline GaV₄S₈ thin layers. Physica Status Solidi - Rapid Research Letters, 2011, 5, 53-55.	1.2	23
63	Structural studies of a cubic, high-temperature (Î±) polymorph of Pb2GeS4 and the isostructural Pb2â^'xSnxGeS4â^'ySey solid solution. Journal of Alloys and Compounds, 2002, 335, 105-110.	2.8	22
64	Design and magnetic properties of new compounds containing iron 2D building blocks of the perovskite type. Solid State Sciences, 2005, 7, 936-944.	1.5	22
65	P-type transparent conductors Sr1â^'xNaxFCuS and SrF1â^'xOxCuS: design, synthesis and physical properties. Journal of Materials Chemistry, 2006, 16, 4165-4169.	6.7	22
66	Synthesis and Structure Determination of La8Ti10S24O4. Journal of Solid State Chemistry, 1998, 136, 46-50.	1.4	21
67	Synthesis of Ni-poor NiO nanoparticles for p-DSSC applications. Solid State Sciences, 2016, 54, 37-42.	1.5	21
68	Preparation by electrophoretic deposition of molybdenum iodide cluster-based functional nanostructured photoelectrodes for solar cells. Electrochimica Acta, 2019, 317, 737-745.	2.6	21
69	Preparation and Crystal Structure Determination of La20Ti11S44O6. Journal of Solid State Chemistry, 1995, 120, 164-169.	1.4	20
70	Dielectric breakdown and current switching effect in the incommensurate layered compound(LaS)1.196VS2. Physical Review B, 2006, 73, .	1.1	20
71	The first dye-sensitized solar cell with p-type LaOCuS nanoparticles as a photocathode. RSC Advances, 2015, 5, 60148-60151.	1.7	20
72	Modulation of Defects in Semiconductors by Facile and Controllable Reduction: The Case of p-type CuCrO₂ Nanoparticles. Inorganic Chemistry, 2016, 55, 7729-7733.	1.9	20

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73	Structure of the water-splitting photocatalyst oxysulfide Î±-LaOInS₂ and ab initio prediction of new polymorphs. Chemical Communications, 2020, 56, 1645-1648.	2.2	20
74	Cation Deficient Layered Ruddlesdenâ"Popper-Related Oxysulfides La₂LnMS₂O₅ (Ln = La, Y; M = Nb, Ta). Inorganic Chemistry, 2007, 46, 9584-9590.	1.9	19
75	Electrical characterizations of resistive random access memory devices based on GaV4S8 thin layers. Thin Solid Films, 2013, 533, 61-65.	0.8	19
76	Preparation of nitrogen doped zinc oxide nanoparticles and thin films by colloidal route and low temperature nitridation process. Solid State Sciences, 2016, 54, 30-36.	1.5	19
77	Temperature and size dependence of time-resolved exciton recombination in ZnO quantum dots. Applied Physics Letters, 2011, 99, .	1.5	18
78	Control of resistive switching in AM₄Q₈narrow gap Mott insulators: A first step towards neuromorphic applications. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 239-244.	0.8	18
79	Synthesis, X-ray and optical characterizations of two new oxysulfides: LaInS2O and La5In3S9O3. Journal of Solid State Chemistry, 2004, 177, 1053-1059.	1.4	17
80	Unravelling the origin of the giant Zn deficiency in wurtzite type ZnO nanoparticles. Scientific Reports, 2015, 5, 12914.	1.6	17
81	Metalâ€"insulator transitions in (V1-xCrx)2O3 thin films deposited by reactive direct current magnetron co-sputtering. Thin Solid Films, 2016, 617, 56-62.	0.8	17
82	Misfit Layer Compounds: A Platform for Heavily Doped 2D Transition Metal Dichalcogenides. Advanced Functional Materials, 2021, 31, 2007706.	7.8	17
83	Resistive Switching Induced by Electric Pulses in a Single-Component Molecular Mott Insulator. Journal of Physical Chemistry C, 2015, 119, 2983-2988.	1.5	15
84	A Topochemical Approach to Synthesize Layered Materials Based on the Redox Reactivity of Anionic Chalcogen Dimers. Angewandte Chemie - International Edition, 2018, 57, 13618-13623.	7.2	15
85	Determination of the modulated structure of the misfit layer compound (LaS)1.196VS2. Materials Research Bulletin, 2005, 40, 125-133.	2.7	14
86	In-plane magnetic penetration depth in NbS2. Physical Review B, 2011, 84, .	1.1	14
87	Electric field induced avalanche breakdown and non-volatile resistive switching in the Mott Insulators AM4Q8. European Physical Journal: Special Topics, 2013, 222, 1046-1056.	1.2	14
88	Ultrafast filling of an electronic pseudogap in an incommensurate crystal. Physical Review B, 2013, 87, .	1.1	14
89	X-ray study of femtosecond structural dynamics in the 2D charge density wave compound 1T-TaS2. Physica B: Condensed Matter, 2015, 460, 100-104.	1.3	14
90	Experimental and Theoretical Evidences of p-Type Conductivity in Nickel Carbodiimide Nanoparticles with a Delafossite Structure Type. Inorganic Chemistry, 2017, 56, 7922-7927.	1.9	14

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91	Relaxation of a Spiking Mott Artificial Neuron. Physical Review Applied, 2018, 10, .	1.5	14
92	Negative Colossal Magnetoresistance Driven by Carrier Type in the Ferromagnetic Mott Insulator GaV₄S₈. Chemistry of Materials, 2015, 27, 4398-4404.	3.2	13
93	Domain-size effects on the dynamics of a charge density wave in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>1</mml:mn><mml:mi mathvariant="normal">T</mml:mi><mml:mtext>â^'</mml:mtext><mml:msub><mml:mi>TaS</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math> Physical Review B, 2017, 96, .	1.1	13
94	Synthesis and structure determination of a new cerium titanium oxysulfide [Ce20Ti11S44O6]. Materials Research Bulletin, 1997, 32, 1181-1192.	2.7	12
95	Synthesis and Structure Determination of Sm3NbSe3O4. Journal of Solid State Chemistry, 1998, 137, 122-126.	1.4	12
96	Band structure and electronic properties of the incommensurate misfit compound. Journal of Physics Condensed Matter, 1999, 11, 2887-2900.	0.7	12
97	High-pressure X-ray diffraction study of 1T-TaS2. Physica B: Condensed Matter, 2012, 407, 1704-1706.	1.3	12
98	Design of metastable oxychalcogenide phases by topochemical (de)intercalation of sulfur in La2O2S2. Nature Communications, 2021, 12, 3605.	5.8	12
99	Ba2F2Fe2+0.5Fe3+S3: A Two-Dimensional Inhomogeneous Mixed Valence Iron Compound. Inorganic Chemistry, 2008, 47, 1648-1652.	1.9	11
100	Anisotropy and temperature dependence of the first critical field in 2Hâ€“NbS2. Physica B: Condensed Matter, 2012, 407, 1813-1815.	1.3	11
101	Crystal structure and chemical bonding in the mixed anion compound BaSF. Dalton Transactions, 2017, 46, 16244-16250.	1.6	11
102	First demonstration of â€œLeaky Integrate and Fireâ€•artificial neuron behavior on (V0.95Cr0.05)2O3 thin film. MRS Communications, 2018, 8, 835-841.	0.8	11
103	Extreme in-plane upper critical magnetic fields of heavily doped quasi-two-dimensional transition metal dichalcogenides. Physical Review B, 2021, 104, .	1.1	11
104	Incommensurate Structure of a Lillianite-Type Samarium Chromium Sulfide Sm2/3Cr2S4. Journal of Solid State Chemistry, 1996, 127, 295-301.	1.4	10
105	Synthesis and crystal structure of two new oxychalcogenides: Eu5V3S6O7 and La10Se14O. Materials Research Bulletin, 2002, 37, 1895-1905.	2.7	10
106	Electric Pulse Induced Resistive Switching in the Narrow Gap Mott Insulator GaMo₄S₈. Key Engineering Materials, 2014, 617, 135-140.	0.4	10
107	Combined First-Principles Calculations and Experimental Study of the Phonon Modes in the Multiferroic Compound GeV₄S₈. Journal of Physical Chemistry C, 2017, 121, 3522-3529.	1.5	10
108	Electronic properties of the (las)1.18vs2 incommensurate misfit compound.. Synthetic Metals, 1999, 103, 2640-2643.	2.1	9

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109	Synthesis of lightâ€coloured nanoparticles of wide band gap pâ€type semiconductors CuGaO₂ and LaOCuS by low temperature hydro/solvothermal processes. Physica Status Solidi (A) Applications and Materials Science, 2010, 207, 1642-1646.	0.8	9
110	Deposition by radio frequency magnetron sputtering of GaV4S8 thin films for resistive random access memory application. Thin Solid Films, 2013, 533, 54-60.	0.8	9
111	A p-Type Zinc-Based Metalâ€“Organic Framework. Inorganic Chemistry, 2017, 56, 6208-6213.	1.9	9
112	Non-volatile resistive switching in the Mott insulator (V1âˆ’xCrx)2O3. Physica B: Condensed Matter, 2018, 536, 327-330.	1.3	9
113	Coherent and Incoherent Tunneling into Yu-Shiba-Rusinov States Revealed by Atomic Scale Shot-Noise Spectroscopy. Physical Review Letters, 2022, 128, .	2.9	9
114	A mixed-valent niobium oxysulfide, La2Nb3S2O8. Acta Crystallographica Section C: Crystal Structure Communications, 2003, 59, i55-i56.	0.4	7
115	Deposition of GaV₄S₈ thin films by H₂S/Ar reactive sputtering for ReRAM applications. Journal Physics D: Applied Physics, 2014, 47, 065309.	1.3	7
116	Ba₂F₂Fe_{1.5}Se₃: An Intergrowth Compound Containing Iron Selenide Layers. Inorganic Chemistry, 2016, 55, 2923-2928.	1.9	7
117	Unexplored reactivity of (S_n)^{2âˆ’} oligomers with transition metals in low-temperature solid-state reactions. Chemical Communications, 2019, 55, 6189-6192.	2.2	7
118	Prediction of a New Layered Polymorph of FeS₂ with Fe³⁺S^{2â€“}(S₂^{2â€“})_{1/2} Structure. Journal of Physical Chemistry Letters, 2020, 11, 8861-8866.	2.1	7
119	Competition between V2O3 phases deposited by one-step reactive sputtering process on polycrystalline conducting electrode. Thin Solid Films, 2020, 705, 138063.	0.8	7
120	Re-examination of yushkinite: chemical composition, optical properties and interlayer charge transfer. Mineralogical Magazine, 1999, 63, 879-889.	0.6	5
121	A gadolinium and niobium oxide sulfide, Gd3NbS3O4. Acta Crystallographica Section E: Structure Reports Online, 2003, 59, i101-i102.	0.2	5
122	Studies on two-gap superconductivity in 2Hâ€“NbS2. Physica C: Superconductivity and Its Applications, 2010, 470, S719-S720.	0.6	5
123	Relation between Thermally Induced Structural Distortions and Electronic Properties of the Layered Misfit Chalcogenide (LaS)1.196VS2. Journal of Physical Chemistry C, 2014, 118, 19273-19279.	1.5	5
124	Two-Gap Superconductivity in 2H-NbS₂. Acta Physica Polonica A, 2010, 118, 1024-1025.	0.2	5
125	A new lanthanum titanium oxysulfide, La16Ti5S17+xO17, withxâ€…=â€…0.75â€…(9). Acta Crystallographica Section C: Crystal Structure Communications, 2003, 59, i63-i64.	0.4	4
126	Impact of Nanostructuration on the Chemical Composition of Nickel Oxide Nanoparticles. Inorganic Chemistry, 2019, 58, 15004-15007.	1.9	4

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